

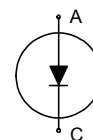
Fast switching diode

Features:

- 600V Emitter Controlled technology 70 μm chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- power modules and discrete devices



Applications:

- SMPS, resonant applications, drives

Chip Type	V_R	I_F	Die Size	Package
SIDC09D60F6	600V	30A	3 x 3 mm ²	sawn on foil

Mechanical Parameters

Raster size	3 x 3	mm ²
Area total	9	
Anode pad size	2.518 x 2.518	
Thickness	70	μm
Wafer size	150	mm
Max. possible chips per wafer	1612	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, $\leq 250\mu\text{m}$	
Reject ink dot size	$\varnothing$ 0.65mm; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C	



SIDC09D60F6

Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$	600	V
Continuous forward current	I_F	$T_{vj} < 150\text{ °C}$	¹⁾	A
Maximum repetitive forward current	I_{FRM}	$T_{vj} < 150\text{ °C}$	60	
Junction temperature range	T_{vj}		-40...+175	°C
Operating junction temperature	T_{vj}		-40...+150	°C
Dynamic ruggedness ²⁾	P_{max}	$I_{Fmax} = 60\text{ A}, V_{Rmax} = 600\text{ V},$ $T_{vj} \leq 150\text{ °C}$	tbd	kW

¹⁾ depending on thermal properties of assembly

²⁾ not subject to production test - verified by design/characterisation

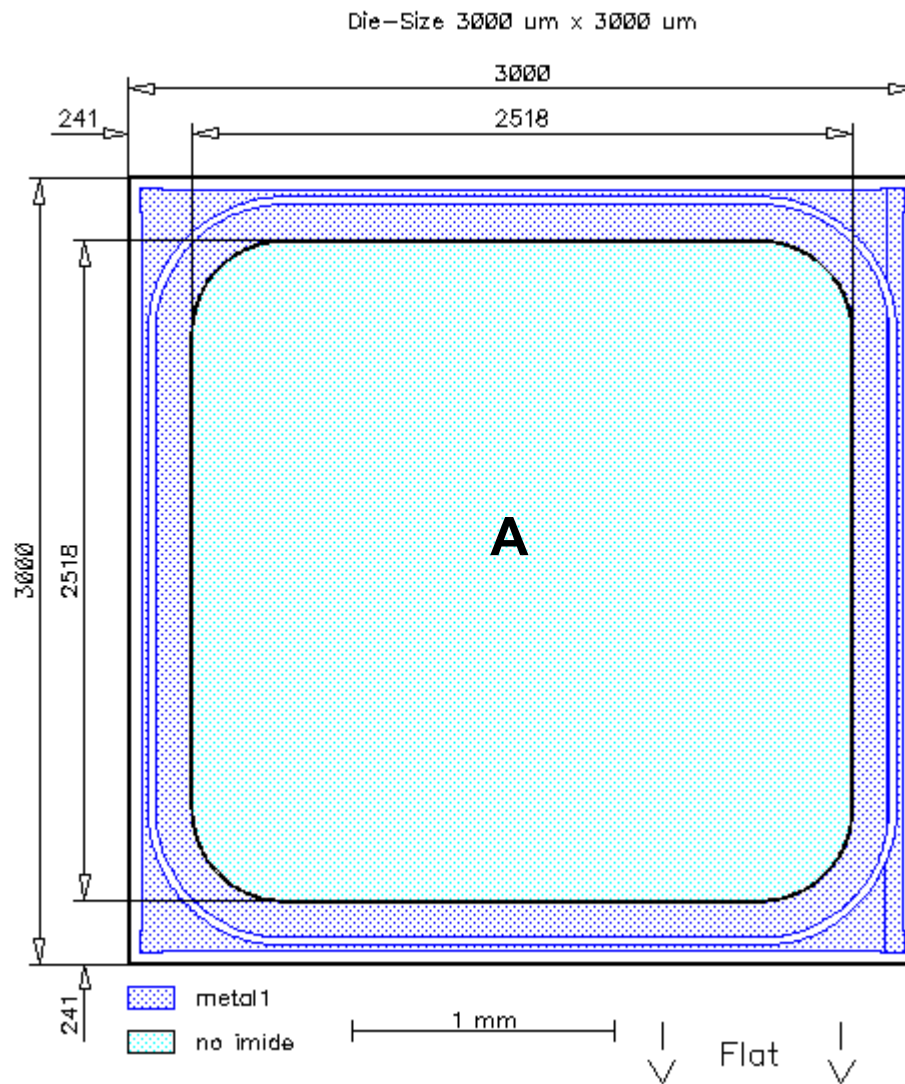
Static Characteristic (tested on wafer), $T_{vj} = 25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse leakage current	I_R	$V_R = 600\text{ V}$			27	µA
Cathode-Anode breakdown Voltage	V_{BR}	$I_R = 1.5\text{ mA}$	600			V
Diode forward voltage	V_F	$I_F = 30\text{ A}$		1.6		V

Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

Chip Drawing



A: Anode pad



SIDC09D60F6

Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date
2.2	Max. possible chips per wafer change to 1612 pcs	03.09.2010

Published by
Infineon Technologies AG
81726 Munich, Germany
© 2010 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.